

### Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

### Listing of Claims

1. **(Currently Amended)** A light emitting device comprising:
  - a substrate;
  - a source wiring over said substrate;
  - a gate wiring over said substrate;
  - at least one thin film transistor provided in an intersection of said source wiring and said gate wiring;
  - an insulator over said thin film transistor;
  - a first electrode formed on said insulator;
  - a second electrode formed on said insulator so as not to be in contact with said first electrode; and
  - a light emitting layer formed between said first and second electrodes on said insulator, wherein a distance between said first electrode and said second electrode, which are adjacent to each other, is set to be 200 nm or shorter,
  - wherein a height of at least one of said first and second electrodes is set to be 100 nm to 500 nm,
  - wherein said first and second electrodes are formed directly on the insulator, and
  - wherein said thin film transistor is electrically connected to said first electrode.
2. **(Currently Amended)** A light emitting device comprising:
  - a substrate;
  - a source wiring over said substrate;
  - a gate wiring over said substrate;

at least one thin film transistor provided in an intersection of said source wiring and said gate wiring;

an insulator over said thin film transistor;

a first electrode formed on said insulator;

a second electrode formed on said insulator so as not to be in contact with said first electrode; and

a light emitting layer formed between said first and second electrodes on said insulator;

a passivation film formed over the first and second electrodes with the light emitting layer interposed therebetween; and

a reflective film formed over the first and second electrode with the passivation film interposed therebetween,

wherein said first and second electrodes are formed directly on the insulator, and

~~wherein said first and second electrodes are located so as to produce an electric field in a direction parallel with said substrate, and~~

wherein said thin film transistor is electrically connected to said first electrode.

**3. (Currently Amended)** A light emitting device comprising:

a substrate;

a source wiring over said substrate;

a gate wiring over said substrate;

a switching thin film transistor and a current controlling thin film transistor provided in an intersection of said source wiring and said gate wiring;

an insulator over said switching thin film transistor and said current controlling thin film transistor;

a first electrode formed on said insulator;

a second electrode formed on said insulator so as not to be in contact with said first electrode; and

a light emitting layer formed between said first and second electrodes on said insulator,

wherein said first and second electrodes are formed directly on the insulator, ~~and~~  
wherein said current controlling thin film transistor is electrically connected to first  
electrode,

wherein a cross section of at least one of said first and second electrodes has a trapezoidal  
shape, and

wherein an angle between a side surface of at least one of said first and second electrodes  
and a surface of said insulator is set to be 50° to 70°.

**4. (Currently amended)** A light emitting device comprising:

a substrate;

a source wiring over said substrate;

a gate wiring over said substrate;

at least one thin film transistor provided in an intersection of said source wiring and said  
gate wiring;

a first insulator over said thin film transistor;

a power supply line over said first insulator;

a reflective film over said first insulator;

a second insulator comprising resin over said first insulator and said power supply line;

a first electrode formed on said second insulator;

a second electrode formed on said second insulator so as not to be in contact with said  
first electrode; and

a light emitting layer formed between said first and second electrodes on said second  
insulator,

wherein said source wiring, said power supply line, and said reflective film are formed  
directly on said first insulator,

wherein said first and second electrodes are formed directly on the second insulator, and  
wherein said thin film transistor is electrically connected to said first electrode.

5. (Previously presented) A light emitting device comprising:  
an insulator;  
an anode formed on said insulator;  
a cathode formed on said insulator so as not to be in contact with said anode; and  
a light emitting layer formed between said anode and said cathode on said insulator,  
wherein said light emitting layer comprises a first layer having an electron transport  
property and a hole transport property and a second layer containing a luminescent material, and  
wherein said first layer is formed on said anode, said cathode, and said insulator, and said  
second layer is formed on said first layer.

6. (Previously presented) A light emitting device comprising:  
an insulator;  
an anode formed on said insulator;  
a cathode formed on said insulator so as not to be in contact with said anode; and  
a light emitting layer formed between said anode and said cathode on said insulator,  
wherein said light emitting layer comprises a first layer having an electron transport  
property and a hole transport property and a second layer containing a luminescent material,  
wherein said first layer is formed on said anode, said cathode, and said insulator, and said  
second layer is formed on said first layer, and  
wherein said anode and said cathode are located so as to produce an electric field in a  
direction parallel with said insulator.

7. (Previously presented) A light emitting device comprising:  
an insulator;  
an anode formed on said insulator;  
a cathode formed on said insulator so as not to be in contact with said anode; and  
a light emitting layer formed between said anode and said cathode on said insulator,  
wherein said light emitting layer comprises a first layer having an electron transport

property and a hole transport property and a second layer containing a luminescent material,  
wherein said first layer is formed on said anode, said cathode, and said insulator, and said  
second layer is formed on said first layer, and  
wherein said anode and said cathode are formed into a comb tooth shape on said insulator  
and located such that each tooth of said anode are adjacent to each tooth of said cathode.

8. (Previously presented) A light emitting device comprising:  
an insulator;  
an anode formed on said insulator;  
a cathode formed on said insulator so as not to be in contact with said anode; and  
a light emitting layer formed between said anode and said cathode on said insulator,  
wherein said light emitting layer comprises a first layer having an electron transport  
property and a hole transport property and a second layer containing a luminescent material,  
wherein said first layer is formed on said anode, said cathode, and said insulator, and said  
second layer is formed on said first layer, and  
wherein said anode and said cathode are formed into a spiral shape on said insulator and  
located such that each tooth of said anode are engaged with those of said cathode.

9. (Previously presented) A light emitting device according to any one of claims 1 to 4,  
wherein said light emitting layer comprises a layer having an electron transport property and a  
hole transport property.

10. (**Currently amended**) A light emitting device according to any one of claims 1, 3  
and 5 to 8, wherein a reflective film is provided under said light emitting layer.

11. (**Currently amended**) A light emitting device according to any one of claims 1, 3  
and 5 to 8, wherein said insulator is transparent and a reflective film is provided over said light  
emitting layer.

12. (Previously presented) A light emitting device according to claim 10, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.

13. **(Currently Amended)** A light emitting device according to any one of claims 2 ~~[[1]]~~ to 4, wherein a distance between said first and second electrodes is 200 nm or shorter.

14. **(Currently Amended)** A light emitting device according to any one of claims 1, 2 and ~~[[to]]~~ 4, wherein an angle formed by at least one of a side surface of said first electrode or said second electrode and a surface on said insulator is 30° to 90°.

15. (Previously presented) A light emitting device according to any one of claims 1 to 4, wherein one of said first and second electrodes comprises a material selected from the group consisting of as gold, nickel, palladium, iridium, and cobalt.

16. (Original) A light emitting device according to any one of claims 1 to 8, wherein said light emitting device is incorporated into an electronic device selected from the group consisting of a display device, a video camera, a head mounted display device, an image back device, a goggle type display device, a portable telephone, a sound reproduction device, and a digital camera.

17. **(Currently Amended)** A light emitting device according to claim 3, wherein said first electrode and said second electrode are formed into a comb tooth shape on said insulator and located such that each tooth of said first electrode is ~~[[are]]~~ adjacent to a corresponding ~~[[each]]~~ tooth of said second electrode.

18. **(Currently Amended)** A light emitting device according to claim 4, wherein said first electrode and said second electrode are formed into a spiral shape on said insulator and located such that each portion ~~[[tooth]]~~ of said first electrode is adjacent to a portion ~~are engaged with these~~ of said second electrode.

19. (Previously presented) A light emitting device according to any one of claims 5 to 8, wherein a distance between said anode and said cathode is 200 nm or shorter.

20. (Previously presented) A light emitting device according to any one of claims 5 to 8, wherein an angle formed by at least one of a side surface of said anode or said cathode and a surface on said insulator is 30° to 90°.

21. (Previously presented) A light emitting device according to any one of claims 5 to 8, wherein said anode comprises a material selected from the group consisting of as gold, nickel, palladium, iridium, and cobalt.

22. (Previously presented) A light emitting device according to claim 11, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.

23. **(New)** A light emitting device according to claim 2, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.

24. **(New)** A light emitting device according to claim 4, wherein said reflective film is made of one selected from the group consisting of titanium, aluminum, alloy of titanium and aluminum, silver, or silver alloy.